

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5882	((438/378) or (438/402) or (438/407) or (438/423) or (438/455) or (438/471) or (438/476) or (438/514) or (438/517) or (438/520) or (438/528) or (438/530) or (438/795) or (438/798) or (438/918) or (438/967)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/12 18:27
L2	27	1 and (flash near5 anneal\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 18:37
L3	6780	((438/149) or (438/311) or (438/458) or (438/473) or (438/474) or (438/475) or (438/477) or (438/479) or (438/480) or (438/495) or (438/496) or (438/499) or (438/406) or (438/508) or (438/509) or (438/514) or (438/787) or (438/788)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/12 18:33
L4	19	3 and (flash near5 anneal\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 18:37
L5	9	4 not "27"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 18:37
L6	14	4 not 2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 18:37
S1	6192	((438/149) or (438/311) or (438/458) or (438/473) or (438/474) or (438/475) or (438/477) or (438/479) or (438/480) or (438/495) or (438/496) or (438/499) or (438/406) or (438/508) or (438/509) or (438/514) or (438/787) or (438/788)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/12 18:33

S2	17530	(soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 18:28
S3	0	((((xe adj arc) near2 lamp) same anneal\$3) near10 ((support or second silicon or quartz or semiconductor)near2 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 17:48
S4	0	((((xe adj arc) near2 lamp) same anneal\$3) same ((support or second silicon or quartz or semiconductor)near2 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 17:48
S5	0	((((xe adj arc) near2 lamp) same anneal\$3) same ((support or second or silicon or quartz or semiconductor)near2 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 17:49
S6	0	((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (((xe adj arc) near2 lamp) same anneal\$3) and ((support or second or silicon or quartz or semiconductor)near2 substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 17:49
S7	26	((((xe adj arc) near2 lamp) same anneal\$3) and ((support or second or silicon or quartz or semiconductor)near2 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 17:50
S8	5	((((xe adj arc) near2 lamp) same (anneal\$3 or heat\$3)) near10 (substrate or (support near2 substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 17:52
S9	54	((((xe adj arc) near2 lamp) same (anneal\$3 or heat\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 17:53
S10	0	((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (((xe adj arc) near2 lamp) same (anneal\$3 or heat\$3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 17:53

S11	206	((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 18:03
S12	0	(((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3))) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign))) near3 (substrate or wafer))) and (((438/149) or (438/311) or (438/458) or (438/473) or (438/474) or (438/475) or (438/477) or (438/479) or (438/480) or (438/495) or (438/496) or (438/499) or (438/406) or (438/508) or (438/509) or (438/514) or (438/787) or (438/788)).CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 17:53
S13	34	(((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3))) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign))) near3 (substrate or wafer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 17:53
S14	10693	wafer near2 bond\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 18:19
S15	2450	((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign))) near3 (substrate or wafer)) and (wafer near2 bond\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 18:02
S16	0	((((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign))) near3 (substrate or wafer)) and (wafer near2 bond\$3)) and (((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 18:02
S17	3933068	anneal\$3 or heat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 18:55

S18	1808	(anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 18:05
S19	281	((xe adj arc) near2 lamp)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 18:03
S20	0	((anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3))) and (((xe adj arc) near2 lamp))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 18:04
S21	40	((anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3))) and (lamp near5 intensit\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 18:29
S22	15436	wafer near5 bond\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 18:20
S23	8537	(wafer near5 bond\$3) and (anneal\$3 or heat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 18:20
S24	1232	implant\$ near5 (hydrogen near ion\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 18:27
S25	179	(wafer near5 bond\$3) same (implant\$ near5 (hydrogen near ion\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 18:57
S26	162	((wafer near5 bond\$3) same (implant\$ near5 (hydrogen near ion\$1))) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 18:28

S27	158	((((wafer near5 bond\$3) same (implant\$ near5 (hydrogen near ion\$1))) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))) and (anneal\$3 or heat\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 18:28
S28	2	(((((wafer near5 bond\$3) same (implant\$ near5 (hydrogen near ion\$1))) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))) and (anneal\$3 or heat\$3)) and (lamp near5 intensit\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 19:38
S29	37	(((((wafer near5 bond\$3) same (implant\$ near5 (hydrogen near ion\$1))) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))) and (anneal\$3 or heat\$3)) and lamp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 18:31
S30	366	((wafer near5 bond\$3) and (implant\$ near5 (hydrogen near ion\$1)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 18:58
S31	310	((wafer near5 bond\$3) and (implant\$ near5 (hydrogen near ion\$1))) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 18:58
S32	0	(((((wafer near5 bond\$3) and (implant\$ near5 (hydrogen near ion\$1))) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))) and (((anneal\$3 or heat\$3) same lamp) near5 (support near2 substrate)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 18:59
S33	0	((wafer near5 bond\$3) and (implant\$ near5 (hydrogen near ion\$1))) and (((anneal\$3 or heat\$3) same lamp) near5 (support near2 substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 18:59

S34	0	((anneal\$3 or heat\$3) same lamp) near5 (support near2 substrate)) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 18:59
S35	43	((anneal\$3 or heat\$3) same lamp) near5 (support near2 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 19:01
S36	2013	(anneal\$3 or heat\$3) near3 (support near2 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 19:02
S37	71	((anneal\$3 or heat\$3) near3 (support near2 substrate)) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 19:02
S38	16	((anneal\$3 or heat\$3) near3 (support near2 substrate)) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))) and (implant\$ near5 (hydrogen near ion\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 19:03
S39	1	"5543636".PN.	USPAT	OR	OFF	2004/08/20 19:22
S40	4	("5854123" "5882987" "5953622" "6010579").PN.	USPAT	OR	OFF	2004/08/20 19:23
S41	6	("5374564" "5882987" "6146979" "6251754" "6294814" "6323108").PN.	USPAT	OR	OFF	2004/08/20 19:24
S42	1	("6376806").PN.	USPAT; USOCR	OR	OFF	2004/08/20 19:35
S43	15	("4356384" "4436985" "4707217" "4755654" "5073698" "5577157" "5722761" "5756369" "5811327" "5840118" "5892332" "5893952" "5937282" "6080965" "6144171").PN.	USPAT	OR	OFF	2004/08/20 19:36

S44	335	flash near2 anneal\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 19:52
S45	0	(flash near2 anneal\$3) near5 (support near2 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 19:40
S46	1	(flash near2 anneal\$3) near10 (support near2 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 19:40
S47	1	(flash near2 anneal\$3) same (support near2 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 19:40
S48	7	(flash near2 anneal\$3) and (support near2 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 19:44
S49	0	(flash near2 anneal\$3) near5 (separt\$5 same substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 19:45
S50	0	(flash near2 anneal\$3) near5 separt\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 19:45
S51	0	(flash near2 anneal\$3) near10 separt\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 19:46
S52	2	(flash near2 anneal\$3) near10 (through near5 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 19:47
S53	1	(flash near2 anneal\$3) near10 (through near2 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 19:48

S54	1	(flash near2 anneal\$3) near10 (through same substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 19:48
S55	27	(flash near2 anneal\$3) near10 (substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 19:50
S56	1	(flash near2 anneal\$3) same (hydrogen near2 ion\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/21 16:29
S57	18	flash near2 anneal\$3 and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 19:55
S58	42016	flash near2 anneal\$3 or ((xe adj arc) near2 lamp) or xenon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/21 18:41
S59	20	(flash near2 anneal\$3 or ((xe adj arc) near2 lamp) or xenon) same ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/20 19:56
S60	41728	((xe adj arc) near2 lamp) or xenon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/21 16:30
S61	40914	(soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/21 16:28
S62	869	(((xe adj arc) near2 lamp) or xenon) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/21 16:28
S63	1422	(hydrogen near2 ion\$1) near5 implant\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/21 16:29

S64	47	((((xe adj arc) near2 lamp) or xenon) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)))) and ((hydrogen near2 ion\$1) near5 implant\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/21 16:29
S65	19527	((xe adj arc) near2 lamp) or xenon near3 lamp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/21 16:30
S66	330	(((xe adj arc) near2 lamp) or xenon near3 lamp) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/21 16:30
S67	13	((((xe adj arc) near2 lamp) or xenon near3 lamp) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)))) and ((hydrogen near2 ion\$1) near5 implant\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/21 16:31
S68	35	(flash near2 anneal\$3) near5 (substrate or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 17:25
S69	0	(flash near2 anneal\$3) near10 ((back or bottom) near5 (substrate or wafer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/21 20:54
S70	0	(flash near2 anneal\$3) near10 (imping\$3 near5 (support near2 substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/21 21:31
S71	0	anneal\$3 near10 (imping\$3 near5 (support near2 substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/21 21:32
S72	0	anneal\$3 same (imping\$3 near5 (support near2 substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/21 21:32

S73	0	anneal\$3 same (imping\$3 or though) near5 (support near2 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/21 21:33
S74	10	anneal\$3 same ((imping\$3 or through) near5 (support near2 substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/21 21:35
S75	8	(flash near2 anneal\$3 same ((imping\$3 or through) near5 substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/21 21:35
S76	6752	((438/149) or (438/311) or (438/458) or (438/473) or (438/474) or (438/475) or (438/477) or (438/479) or (438/480) or (438/495) or (438/496) or (438/499) or (438/406) or (438/508) or (438/509) or (438/514) or (438/787) or (438/788)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/04 17:23
S77	0	S76 and (flash near5 anneal\$3) near5 ((quartz or glass) near2 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 17:27
S78	2	(flash near5 anneal\$3) near5 ((quartz or glass) near2 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 17:27